

1 / 7

FIG. 1

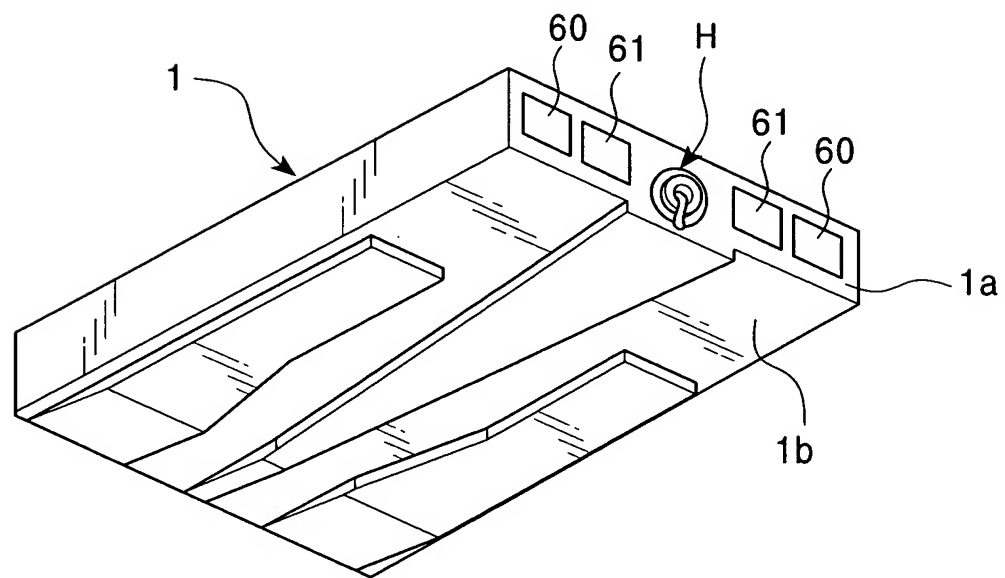
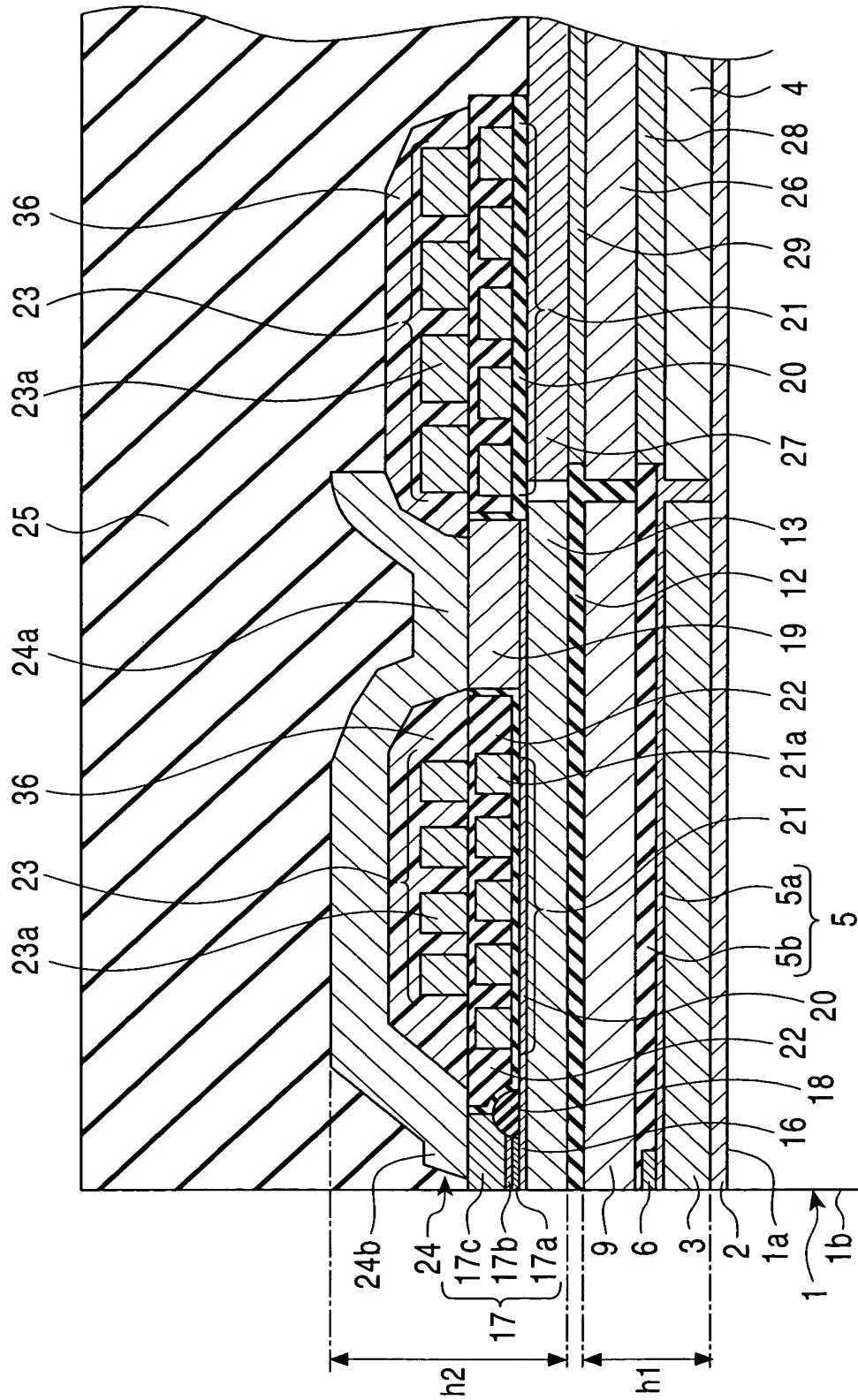


Figure 1 is a cross-sectional view of a semiconductor device. It shows two main structures, one above the other. The upper structure consists of several layers: a base layer (1), followed by layers 2, 3, 4, 5a, 5b, 6, 7, 8, 9, 10, 11, 12, 13, 14, 15, 16, 17a, 17b, 17c, 20, 21, 22, 23, 24, 25, and 26. The lower structure consists of layers 18, 19, 20, 21, 22, 23, 24a, 24b, 25, and 26. Dimensions h1 and h2 are indicated between dashed horizontal lines.

3 / 7

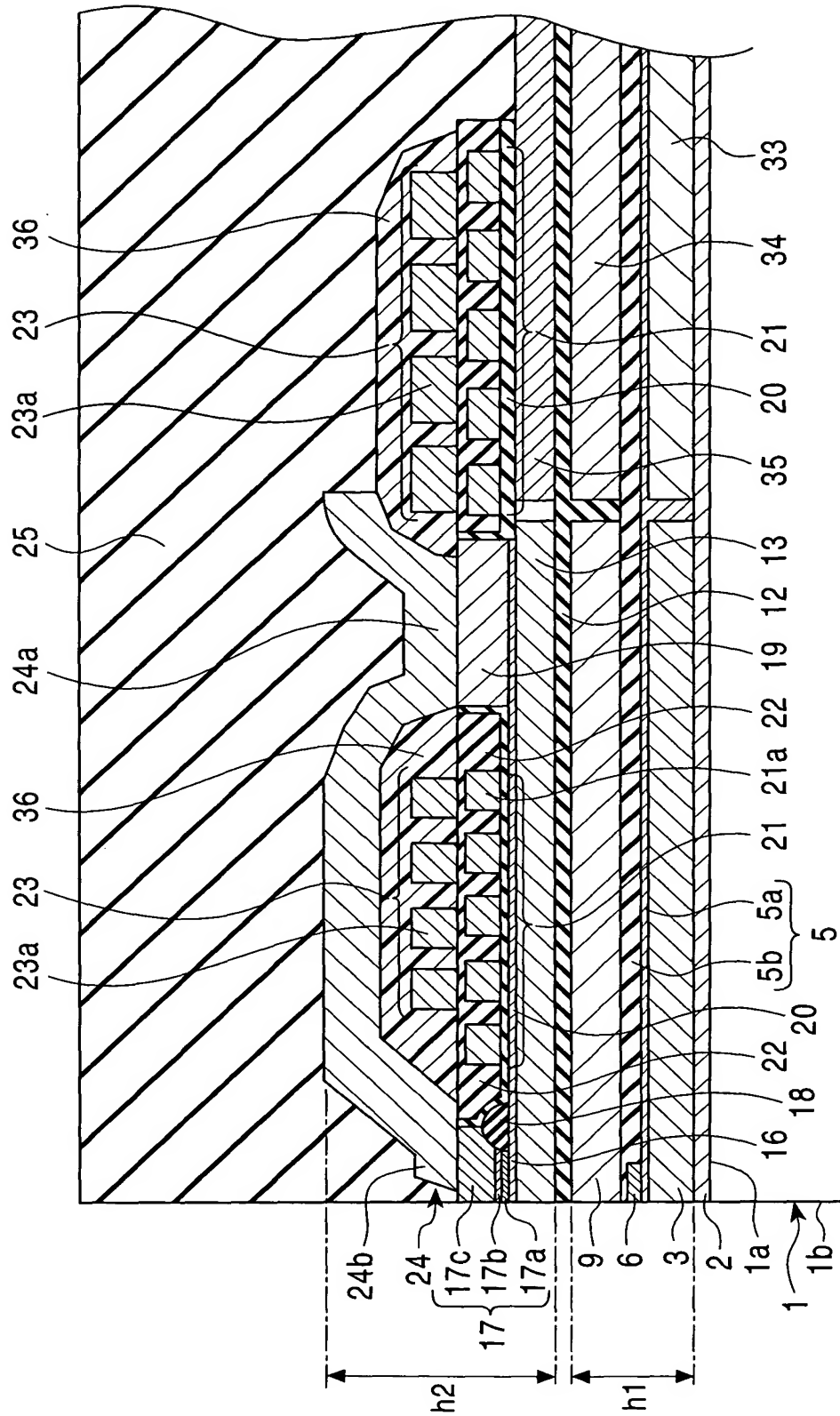
FIG. 3



[illegible]

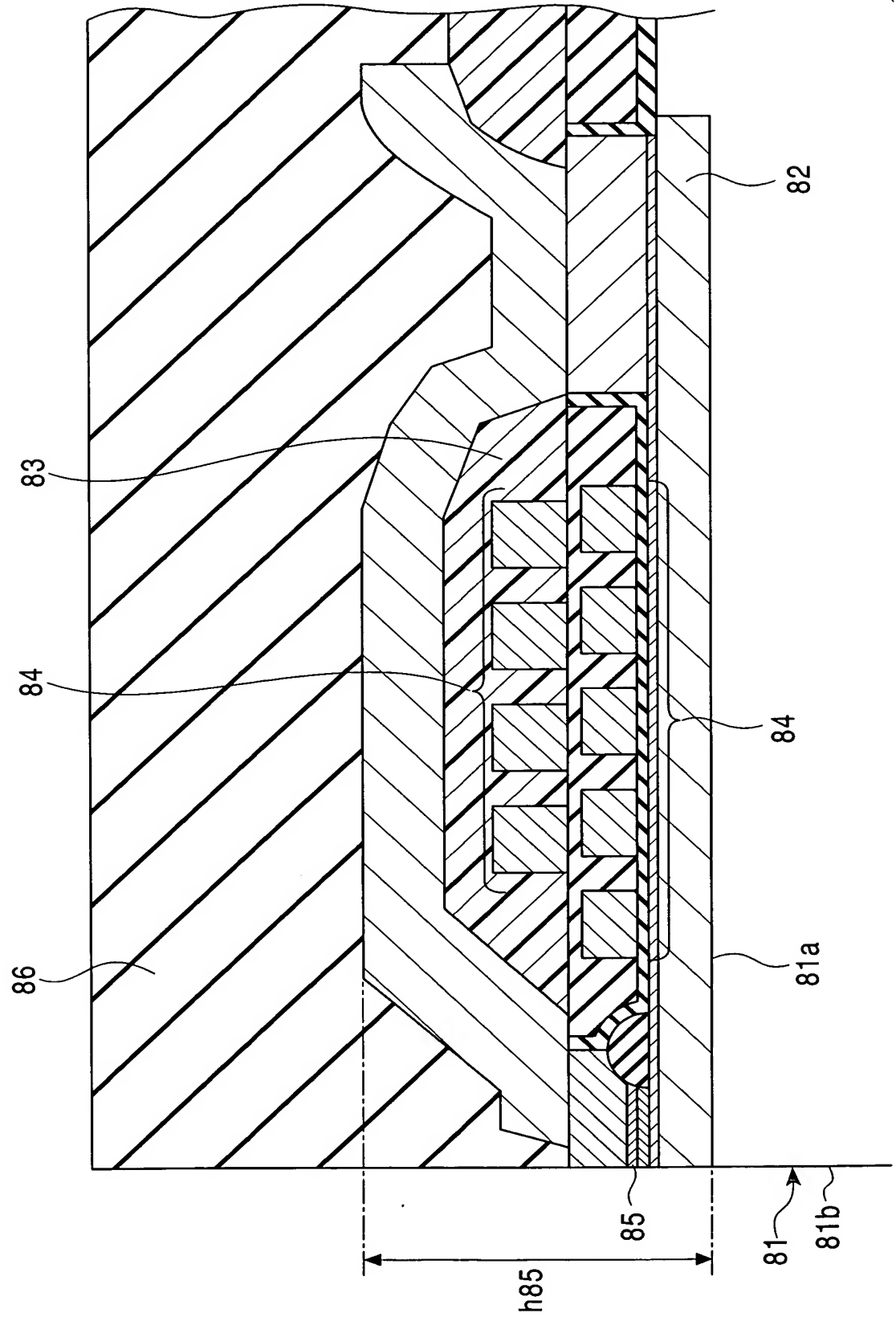
5 / 7

FIG. 5



6 / 7

FIG. 6  
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7 / 7

FIG. 7  
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